# E ect of the C oulom b interaction on the electron relaxation of weakly-con ned quantum dot systems

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### Abstract

We study acoustic-phonon-induced relaxation of charge excitations in single and tunnel-coupled quantum dots containing few con ned interacting electrons. The Full C on guration Interaction approach is used to account for the electron-electron repulsion. Electron-phonon interaction is accounted for through both deform ation potential and piezoelectric eld mechanisms. We show that electronic correlations generally reduce intradot and interdot transition rates with respect to corresponding single-electron transitions, but this elect is lessened by external magnetic elds. On the other hand, piezoelectric eld scattering is found to become the dom inant relaxation mechanism as the number of con ned electrons increases. Previous proposals to strongly suppress electronphonon coupling in properly designed single-electron quantum dots are shown to hold also in multi-electron devices. Our results indicate that few electron orbital degrees of freedom are more stable than single-electron ones.

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#### I. IN TRODUCTION

Recent experiments have appointed coupling to acoustic phonons as the main source of electron relaxation in the excited states of sem iconductor quantum dots (QDs) with weak lateral connement<sup>1,2</sup> and coupled quantum dots (CQDs) with small tunneling energy,<sup>3,4,5</sup> i.e., with the electronic relevant energy scale in the few-meV range. This usually restricts lifetimes to the order of nanoseconds,<sup>1</sup> imposing severe limitations on the performance of QD devices which rely on the coherent dynamics of electron charge states. A prominent example are charge qubits, whose main disadvantage, as compared to spin qubits, is the faster decoherence rate.<sup>1</sup>

As a rst step to eventually gain control over charge relaxation rates, several theoretical works have investigated the fundam ental physics of electron-phonon coupling in QD structures. Bockelm ann described the qualitative e ect of lateral (spatial and m agnetic) con nem ent on the electron transition rates in QD s.<sup>6</sup> The dom ains of deform ation potential (DP) and piezoelectric eld (PZ) interactions, the two main scattering mechanism s leading to interaction with acoustic phonons, were established for both QD and CQD structures.<sup>7,8,9,10</sup> Building on these works, methods to minim ize electron-phonon coupling in QD s and vertically CQD s were recently proposed which may bring electron lifetimes in the range of microseconds, thus making them comparable to usual spin relaxation rates.<sup>7,11,12,13</sup>

Noteworthy, all of the aforem entioned experimental and theoretical works studied charge relaxation at a single-electron (SE) level. So far, multi-electron (ME) systems have been essentially restricted to the context of spin relaxation,<sup>1,2,14,15</sup> and only lately charge relaxation processes in ME systems started to be considered.<sup>16,17</sup> In particular, in Ref. 17 we have investigated C oulomb correlated systems, and we have reported numerical evidence that electronic correlations generally lead to reduced decay rates of the excited electronic states in weakly con ned dots, as compared to independent-particle estimates. This inding suggests that ME devices might better exploit the discrete energy spectrum of QD s.

In this paper, we extend our previous investigation (Ref. 17) analyzing in detail the mechanism sby which C oulom b interaction a ects charge relaxation rates in M E Q D system s. We also investigate the e ect of external magnetic elds on intradot transition rates, and isospin transition rates in M E vertically CQD s. Electron-phonon interaction is included through both D P and PZ scattering channels (the latter was neglected in Ref. 17 as well as

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in m any theoretical investigations).

The paper is organized as follows. In Section II we describe our theoretical model. In Section III we study M E charge relaxation in single Q D s as a function of the lateral (spatial and magnetic) con nement, and interpret the correlation-induced scattering reduction in terms of the SE con guration mixing. The applicability in M E QD s of magnetic-eld-based suggestions for controlling charge relaxation rates, previously reported for SE structures<sup>7,12,13</sup>, is addressed in this section. In Section IV we investigate the e ect of interdot distance on the isospin transition rate of M E vertically CQD s, and nally in Section V we sum marize our results.

#### II. THEORETICAL FORM ULATION

The theoretical model we use is similar to that described in Ref. 7 for single-electron excitations, but now considering N -electron states (N = 1 5). We study disk-shaped QDs where the lateral con nem ent is much weaker than the vertical one, and the dot and surrounding barrier are made of materials with similar elastic properties. Several QD structures reported in the literature t this description.<sup>1,2,18</sup>

A number of useful approximations can be made for such QDs. First, since the weak lateral connement gives inter-level spacings within the range of few meV, only acoustic phonons have signicant interaction with free carriers, while optical phonons can be safely neglected. Second, the elastically homogeneous materials are not expected to induce phonon connement, which allow us to consider only bulk phonons. Finally, the different energy scales of vertical and lateral electronic connement allow us to decouple vertical and lateral electronic connement allow us to decouple vertical and lateral electronic connement allow us to decouple vertical and lateral motion in the building of SE spin-orbitals. We then take a parabolic connement prole in the in-plane (x;y) direction, with single-particle energy gaps h!<sub>0</sub>, which yields the Fock-D arw in states.<sup>19</sup> In the vertical direction (z) the connement is provided by a rectangular quantum well of length  $L_z$ , with the barrier height determined by the band-o set between the QD and barrier materials. The quantum well solutions are derived numerically. Spinorbit coupling is neglected in this work, since the long spin relaxation times measured in QD structures sin lar to those we study here indicate that the spin degrees of freedom are well separated from the orbital ones.<sup>1</sup> Therefore, the SE spin-orbitals can be written as:

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$$(x;y;z;) = n_{m} (x;y)_{q} (z) ;$$
 (1)

where  $n_{m}$  is the n th Fock-D arw in orbital with azim uthal angular momentum m, g is the symmetric quantum well solution with parity g with respect to the rejection about the z = 0 plane, with g = 0 (1) denoting even (odd) parity, and is the spinor eigenvector of the spin z component with eigenvalue (= 1=2). We will also label Fock-D arw in states with the standard notation n l, where l = s; p; d ::: correspond to m = 0; 1; 2:::,respectively.

As for the inclusion of C oulomb interactions, we need to go beyond the H artree Fock approximation in order to include electronic correlations, which are critical in phonon-induced electron scattering processes.<sup>16</sup> M oreover, since we are interested in the relaxation time of excited states, we need to know both ground and excited states with comparable accuracy. Our method of choice is the Full C on guration Interaction approach: the M E wave functions are written as linear combinations  $j_ai = \Pr_i c_{ai}j_i$ , where the Slater determinants  $j_ii = \frac{p_i}{c_i} c_i^j$  jui are obtained by lling in the SE spin-orbitals with the N electrons in all possible ways consistent with symmetry requirements; here  $c^y$  creates an electron in the level . The M E ground and excited states can then be labeled by the total angular momentum z component M = 0; 1; 2:::, total parity G = 0;1, total spin S, and total spin z-projection  $S_z$ . The fully interacting H am iltonian is numerically diagonalized, exploiting orbital and spin symmetries.<sup>20</sup>

W e assume zero tem perature, which su ces to capture the main features of one-phonon processes.<sup>12</sup> At this tem perature, only phonon emission processes are present. W e evaluate the relaxation rate between selected initial (occupied) and nal (unoccupied) M E states, b and a, using the Ferm igolden rule:

$${}_{b!a}^{1} = \frac{2}{h} \sum_{q \ ij}^{X \ X} C_{bi} c_{aj} h_{i} \mathbf{y}_{q} \mathbf{j}_{j} \mathbf{i}^{2} (E_{b} \ E_{a} \ E_{q}); \qquad (2)$$

where the electron states j i ( =  $a_ib$ ) have been written explicitly as linear combinations of Slater determ inants, V <sub>q</sub> is the interaction operator of an electron with an acoustic phonon of m om entum q via deform ation potential ( = D P) or piezoelectric eld ( = P Z) interaction, E stands for the electron state energy and E<sub>q</sub> represents the phonon energy. The electron-phonon interaction matrix element can be written more explicitly as

$$h_{i} \mathbf{y}_{q} \mathbf{j}_{j} \mathbf{i} = \mathbf{M} \quad (\mathbf{q}) h_{i} \mathbf{j} e^{\mathbf{i} \mathbf{q} \mathbf{r}} \mathbf{j}_{j} \mathbf{i}; \tag{3}$$

where the right-m ost term is the electron form factor and M (q) is a prefactor which depends on the scattering mechanism <sup>7</sup>. It is worth noting that, whereas for DP scattering M<sub>DP</sub> /  $p_{jqj}$  for PZ scattering M<sub>PZ</sub> /  $1=p_{jqj}$ . As a result, DP scattering is dominant when the emitted phonon energy is su ciently large, while PZ scattering dominates at small phonon energy. For SE transitions in G aAs QDs, even in the weakly-con ned regime, the DP mechanism usually prevails in the absence of external elds. However, we have recently show n<sup>7</sup> that the PZ mechanism may rapidly become dominant in the presence of a vertical magnetic eld which tends to suppress the single-particle gaps.

One can see from the above expressions that C oulomb interaction in uences electron scattering with phonons in two ways. First, it introduces changes in the electron energy gaps  $E_b = E_a$ , and hence in the energy and momentum of the emitted phonon.<sup>16</sup> Second, it introduces changes in the orbital part of the electron state, hence changing the electron-phonon wave functions coupling. The latter e ect is rejected in Equation (2) through the Slater determ inant coe cients. Indeed, since the total scattering rate is but a weighted sum of SE contributions, the general behavior of SE scattering events will also apply to the ME case. However, the weight of each SE contribution strongly depends on the number of particles, the regime of correlations, and the presence of external elds, so that in portant changes in the ME relaxation rates should be expected when varying these parameters.

In this work we consider mostly relaxation rates corresponding to the fundam ental spinconserving transition in single and coupled QDs, i.e. transitions involving the ground state and the rst excited state with the same (S; S<sub>z</sub>) quantum numbers. This transition could be monitored, e.g., by means of pum p-and-probe techniques,<sup>1,2,14</sup> since relaxation to or from any intermediate state with di erent spin should be much slower and therefore it will barely interfere.

Below we shall investigate  $GaAs/Al_{0.3}Ga_{0.7}As$  QDs, using the following material parameters:<sup>21</sup> electron e ective mass m = 0.067, band-o set  $V_c = 243 \text{ meV}$ , crystal density d = 5310 kg/m<sup>3</sup>, acoustic deformation potential constant D = 8.6 eV, e ective dielectric constant = 12.9, and piezoelectric constant  $h_{14} = 1.41 = 1.41 = 1.0 \text{ V/m}$ . For the sound speed

c, we take into account that in cylindrical QD s m ost of the scattering arises from phonon propagation close to the growth direction.<sup>13</sup> W e then assume that the QD s are grown along the [100] direction and use the corresponding values  $c_{LA} = 4.72$  10m/s and  $c_{TA} = 3.34$  10 m/s.<sup>22</sup> In our calculations we deal with QD s with lateral connement energies which in some cases are rather weak (h!  $_0 < 1 \text{ m eV}$ ). W ell-converged few-body states are obtained for such structures using a basis set composed by the Slater determ inants which result from all possible combinations of 62 SE spin-orbitals with N electrons. D ue to the strong connement in the vertical direction, only the lowest g = 0 (for single QD s) or the lowest g = 0;1 (for CQD s) eigenstates are included in the single-particle basis.

### III. SINGLE QUANTUM DOTS AND MAGNETIC FIELD

In this section we rst study charge relaxation rates in QDs with N interacting electrons as a function of the harm onic lateral con nem ent originated by electrostatic elds, and next consider the e ect of adding a magnetic eld. To study the lateral con nem ent, we vary the characteristic frequency of the con ning parabola in the  $h!_0$  0 6 m eV range, thus moving from a strongly-to a rather weakly-correlated regime. Figure 1 depicts the corresponding results for N = 1 5 electrons in QD s with height  $L_z = 10$  nm. It can be observed that for all N the qualitative shape of the relaxation rate curve is similar to that of the SE case (top panel): it shows two maxima, connected with the PZ and DP scattering mechanisms, and it vanishes at sm all and large con nem ent energies due to the sm all phonon density and sm all electron-phonon coupling, respectively.<sup>6,7,23</sup> Another trend observed in Fig. 1 is the shift of the scattering rate maxim a towards larger con nem ent energies with increasing num ber of electrons, as well as the increasing relative height of the PZ maximum. Both features follow from the increasing density of states with larger N, which leads to sm aller inter-level spacing and, therefore, to larger h! 0 values associated with a given phonon energy. We illustrate this in Fig. 1 with downward arrows to point at the con nement energies which give two selected phonon energies,  $E_q = 1.3$  (solid arrowhead) and  $E_q = 2.0$  meV (empty arrowhead). It can be seen that there is a shift towards larger h! 0 values with increasing N.<sup>24</sup> An important implication of this result is that PZ scattering, which is negligible except at very weak con nem ent energies in the SE picture, may actually become the dom inant scattering mechanism for usualQD con nement energies in the ME case (see, e.g.,  $h!_0 = 2$ 

m eV in the N = 5 picture). In light of this, som e of the estim ates in previous investigations, which studied electron-phonon coupling in weakly-con ned QDs considering DP interaction only, may need a revision.<sup>16,17</sup>

One also observes in Fig. 1 that the phonon energy which gives maximum scattering is approximately constant, regardless of the number of electrons and lateral connement. For example,  $E_q = 1.3 \text{ meV}$  for the DP maximum. This indicates that the scattering is mainly determined by the electron-phonon coupling along the vertical direction: indeed, at  $E_q = 1.3 \text{ meV}$  the longitudinal acoustic phonon wavelength gives maximum coupling with the electron wave function in the quantum well, which does not depend on h!<sub>0</sub> and is weakly a ected by Coulomb interactions.

Figure 1 shows that the excited state lifetim es depend strongly on the number of carriers (note the di erent vertical scale of each panel), the shorter lifetim es being shown by the N = 1 case. As a matter of fact, the N = 1 transition, which corresponds to the p ! s relaxation, represents the independent-particle limit of the ME cases shown in the same gure. For example, for N = 2 an independent particle lling gives a (M = 0; S = 0)ground state, with the two electrons occupying the s spin-orbitals, and a (M = 1; S = 0)excited state, with one electron in the s orbital and another in the p orbital (see electronic con guration diagrams in Fig.2(a)). Thus, the transition involves a one-electron scattering p ! s orbital, while the other electron remains as a spectator. Sim ilar reasonings apply to N = 3 5. Therefore, Fig. 1 shows that the C oulom b-interaction-free relaxation rate (N = 1 panel) generally gives an upper-bound to the actual rate when electron-electron interaction is taken into account. This result holds for all number of particles studied and m ost con nem ent strengths, although the trend is non-m onotonic with N.

The reduction of the relaxation rate noted above can be explained in terms of SE con gurations mixing. In order to illustrate this, we analyze in detail the N = 2 and N = 3 cases in Fig. 2, where panel (a) represents the electronic con gurations of the rst excited and ground states which follow from an independent-particle lling, while panel (b) represents the two most important con gurations contributing to the same states when C oulom b interaction is included. By comparison, one can see that in the non-interacting picture only the p ! s transition takes place, whereas in the interacting picture it is partially replaced by the d ! s and d ! p transitions. We then compare the relaxation rates of the individual SE scattering processes [panel (c)], xing the transition energy

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 $E_q = h!_0$  in all cases in order to ensure that the comparison considers orbital e ects only. One can see that p! s is the fastest transition. Therefore, when it is partially replaced by d! s and d! p the overall relaxation rate is reduced. O by by the stronger the m ixing of con gurations the larger the reduction. This explains why the N = 3 scattering rate is well below that of N = 2: the ground state electrons already occupy the p-shell and the kinetic energy di erence with respect to the excited states is then much sm aller, which allows stronger C oulom b-induced m ixing. A nalogous logic can be used to explain the scattering reduction in the N > 3 system s.

We next investigate the e ect of a magnetic eld B, applied along the vertical direction of the QD, on the ME relaxation rate. The magnetic eld is expected to introduce new physics because it strongly modiles the SE energy levels, which now draw the well-known Fock-D arw in spectrum <sup>19</sup>. In particular, the states involved in the fundamental transition converge to the same (lowest) Landau level. This has in portant in plications on the energy of the emitted phonon -which is reduced-, the regime of electronic correlations -which become e stronger- and the SE con gurations of the low -lying ME states -which dier from those at zero magnetic eld-. In Figure 3 we plot the relaxation rate corresponding to N = 2 in a QD with lateral con nement h!  $_0$  = 2 m eV and width  $L_z$  = 10 nm. We show the fundamental transition both in the singlet (S = 0) sector (solid lines) and in the triplet (S = 1) sector. We also compare the interacting and non-interacting case (thick and thin lines, respectively).

It can be seen in the gure that the shape of the M E curves is again qualitatively similar to that of the SE ones. From previous investigations, we know that the scattering rate at elds exceeding a few Tesla is largely determ ined by the PZ scattering channel.<sup>7</sup> In addition, we note that the correlation-induced reduction of the relaxation rates changes with the eld. Indeed, the factor of reduction tends to decrease as B increases, and at some point (B 10.5 T for the singlet sector, B 13 T for the triplet sector) the e ect of correlations is reversed, so that a small enhancement is found instead of the more common reduction. This reversal in the behavior can be explained in term softherm ixing of congurations in the presence of a magnetic eld. When no C oulomb interaction is considered only the  $p_+$  ! s SE transition contributes to the total scattering, as shown in Fig. 4 (a). However, if we take into account the C oulomb-induced m ixing between the two most important congurations, Fig. 4 (b), new relaxation channels are opened, notably the  $d_+$  ! s and  $d_+$  !  $p_+$  SE transitions. The increasing relative weight of these transitions with B, along with the fact that the d<sub>+</sub> !  $p_+$  transition becomes faster than the  $p_+$  ! s one at su ciently strong elds [Fig. 4 (c)], justify the observation that electronic correlations at high magnetic eld yield slightly increased relaxation rates.<sup>25</sup> Yet, it may be worth pointing out that this takes place when the states involved in the transition have almost converged in energy (see inset in Figure 3). Indeed, at such magnetic eld values the investigated transitions are not the fundamental transition anym ore, since higher-angularm omenta states have already come down in energy (this occurs at about B = 4 T in the QD we study, when the (M = 2; S = 1) level becomes the ground state).

Recently, it has been suggested that electron-phonon coupling can be tailored in weakly-con ned QDs and CQDs, so that SE lifetimes may be increased by orders of m agnitude.<sup>7,11,12,13</sup> The physical idea behind this possibility is to achieve an anti-phase relation between the phonon wave and the electron wave function along the growth direction of the QD structure, i.e., to make the phonon wavelength along z a divisor of the quantum well width, thereby reducing strongly the value of the form factor in Equation 3. The phonon wavelength can be controlled through the lateral con nement, which is in turn determ ined either by electrostatic elds or by an axial magnetic eld. The latter reduces the energy splitting between the low-lying SE states and thus increases the phonon wavelength in a controllable manner.<sup>7,12,13</sup> The possibility of using external elds to suppress charge relaxation also in ME system s m ay pose a signi cant support for the eventual fabrication of ME QD devices with small decoherece rates. However, the applicability is not straightforward: indeed, as m entioned before, the energy of the em itted phonon corresponding to the fundamental transition decreases with increasing N, owing to the larger density of states.<sup>26</sup> As a result, the phonon wavelength may be too long to ever match anti-phase relation with the electron wave function in the growth direction. In order to explore this issue, in Fig. 5 we represent the charge relaxation rate in a QD with  $h!_0 = 5 \text{ meV}$  and  $L_z = 15 \text{ nm}$  with N = 2 and N = 3 electrons. For N = 2, two scattering m in im a show up at B = 0.6 T and B = 2:4 T. These are the same values as found in the  $N = 1 \text{ case}^{7}$ , which suggests that the N = 2 scattering is well described as an independent-particle event. However, the N = 3picture only shows one minimum at B = 0.55 T (the dip at B 4 T is simply due to the crossing between the (M = 1; S = 1=2) and (M = 2; S = 1=2) energy levels). This is a clear manifestation of phonon energy reduction due to Coulom b interactions. For a larger num ber

of electrons (not shown), when the density of states is still higher, the magnetic eld brings about frequent changes of energy levels with di erent sym metry, so that tuning the emitted phonon energy is no longer feasible. We then conclude that B-induced suppression of charge relaxation rates holds for QD s with a small enough number of electrons, but it rapidly loses e ciency as the number of particles increases, ow ing to the increasing density of states.

#### IV. COUPLED QUANTUM DOTS

In this section we study charge relaxation rates corresponding to N -electron isospin transitions in vertically CQDs as a function of the interdot barrier thickness  $L_b$ . The two QDs are supposed to be identical.<sup>27</sup> W e focus on the transition between the lowest symmetric (G = 0) and antisymmetric (G = 1) solutions of the double quantum well with the spin quantum numbers of the ground state, i.e., the fundamental isospin (interdot) transition. This is indeed the fundamental transition of the system when the tunneling energy is smaller than the lateral con nement energy of the constituent QDs.

Figure 6 illustrates the results for a CQD structure with  $L_z = 5 \text{ nm}$ ,  $h!_0 = 5 \text{ m eV}$  and N = 1;2;3 electrons. Solid lines indicate the total scattering rate, while dashed and dotted lines represent the contribution coming separately from DP and PZ interactions, respectively. A s for the intradot transition case, it is worth noting that the N = 1 calculation represents the independent-particle lim it of the N = 2 and N = 3 system s. Since the maximum scattering rate of the N = 2 (N = 3) system is smaller than that of N = 1 by a factor of about 4 (2), we conclude that interdot transitions also bene t from a correlation-induced reduction of the scattering rates. Such reduction can be interpreted in term s of con guration m ixing in analogous manner to the intradot case described in the previous section.

W e note in Fig. 6 that the shape of the scattering rate curve is qualitatively sim ilar for N = 1 and N = 3, with a dom inating and oscillating DP scattering intensity at sm all barrier thickness, and a PZ contribution which becomes dom inant as the barrier thickness exceeds

10 nm  $^{7}$  In contrast, the shape signi cantly di ers for N = 2, where the PZ contribution is m issing. A ctually, a close inspection reveals that it has been suppressed by alm ost four orders of m agnitude. This striking result cannot be interpreted as a consequence of correlations on the electron wave function, as in previous sections, because the orbital part of the electronphonon interaction m atrix element is identical for DP and PZ scattering m echanism s (see Eq. 3), and therefore the e ect should be apparent also for DP scattering. Therefore, the origin must be connected with the e ect of C oulomb interaction on the emitted phonon energy.

To better understand this result, in Fig. 7 we compare the  $L_{\rm b}$  dependence of the tunneling energy, and hence that of the emitted phonon, for N = 2 with and without Coulomb interaction. Clearly, Coulomb interaction is responsible for a signi cantly faster reduction of the tunneling energy. Consequently, the values of  $L_{\rm b}$  which would lead to maximum PZ scattering for non-interacting electrons (e.g., L<sub>b</sub> 11 nm), are now associated with very sm all phonon energies. As a result, the phonon density of states is very sm all and the electron-phonon coupling is strongly reduced. This behavior is no longer found in the N = 3system. An interpretation of this observation is provided in the diagram s of Fig. 7, where we show the dom inant SE con gurations for the interacting and non-interacting electrons. In the absence of C oulom b interaction, the only con guration for the G = 0 state has two electrons in the lowest SE symmetric orbital  $(^{2})$ . Similarly, for the G = 1 state the only signi cant con guration is that with one electron in the lowest SE symmetric orbital and another in the lowest antisymmetric orbital ( ). However, when Coulomb interaction is included for G = 0 we mostly obtain a linear combination of  $^{2}$  and ()<sup>2</sup> con gurations. The thicker the barrier, the sm aller the tunneling energy and the larger the mixing between these two con gurations. In the limit where both con gurations have equal weight, the G = 0state will be degenerate with the G = 1 one. In other words, C oulom b interaction tends to make G = 0 and G = 1 solutions converge in energy with increasing L<sub>b</sub>. This is not possible for N = 3 because the unpaired electron prevents a similar mixing of con gurations which orbitals while preserving the total parity quantum number. Therefore, the only use and signi cant electronic con guration for G = 0 and G = 1 are <sup>2</sup> and ()<sup>2</sup>, respectively. The transition between these two con qurations can be envisaged as the relaxation of a to orbitals, which explains the similar behavior of N = 3 as compared single hole from to N = 1.

V. SUMMARY

We have investigated the e ect of C oulom b interaction on the charge relaxation rates of disk-shaped QD systems with few electrons, due to incoherent coupling with acoustic phonons. We have studied both intradot transitions in single QDs and interdot (isospin) transitions in vertically CQDs. Coulomb interaction a ects the scattering rates in two ways: rst, it changes the emitted phonon energy and momentum, and second, it changes the electron wave function through electronic correlations. Both e ects have a signi cant in uence on the electron relaxation rate in a way that generally leads to a reduction of the intradot and interdot transition rates. This trend is gradually quenched by axialm agnetic elds. On the other hand, the increasing density of states with higher num ber of particles reduces the energy of the emitted phonons, which renders PZ interaction increasingly in portant, so that it may eventually become the dom inant scattering mechanism even at zero magnetic eld. We have nally shown that the suppression of electron scattering in weakly-con ned QDs, which was recently suggested for SE system s,<sup>7,12,13</sup> also applies to multi-electron QDs with a su ciently small number of particles.

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- <sup>23</sup> The suppression of the relaxation rate at sm all con nem ent energies for N = 1 is not seen in Figure 1 because it occurs for characteristic frequencies h!<sub>0</sub> < 0.1 m eV, but it is apparent e.g. in Figure 2 (c).
- <sup>24</sup> The large shift from N = 2 to N = 3 is due to the occupation of the p-shell by the ground state electrons, which greatly reduces the kinetic energy di erence with respect to the excited states.

- <sup>25</sup> It may be worth pointing out that the phonon energy of the plotted transitions in Figure 4 is identical, so the di erent rates are due to orbital e ects only.
- <sup>26</sup> Note that the role of electronic correlations is secondary for this discussion since we are concerned about the electron wave function in the vertical direction only, which is the rst solution of the quantum well for all low-lying QD states due to the strong vertical con nem ent.
- $^{27}$  The scattering rates of SE CQDs with slightly an isotropic QDs have been studied in Ref. 7.



FIG. 1: Charge relaxation rate vs lateral con nem ent for a QD with vertical width  $L_z = 10$  nm led with N = 1 to N = 5 electrons. Solid lines: total scattering rate. Dashed line: DP contribution. Dotted lines: PZ contribution. Note the di erent vertical scale in each panel. Next to the right axis, we indicate the quantum numbers (M;S) of the states involved in the transition. The downward arrows in each panel point at the con nem ent energy leading to emitted phonon energies of 1:3 (solid arrowheads) and 2 m eV (empty arrowheads). Inset in the top panel: SE con gurations involved in the N = 1 transition.



FIG.2: SE electronic con gurations (Slater determ inants) involved in the fundam ental transition for the QDs of Fig.1 for N = 2 and N = 3 for (a) non-interacting and (b) interacting electrons. In the interacting case only the two most weighted con gurations are shown. (c) SE scattering rates vs lateral con nem ent energy between selected Fock-D arw in orbitals at xed phonon energy  $E_q = h!_0$ .



FIG. 3: Charge relaxation rate vs magnetic eld for the lowest singlet (solid lines) and triplet (dashed lines) transitions for N = 2 in a QD with  $L_z = 10$  nm and  $h!_0 = 2$  meV. Thick lines: interacting case. This lines: non-interacting case. Inset: lowest-lying energy levels and their quantum numbers (M;S); arrows indicate the transitions under study.



FIG. 4: SE electronic con gurations (Slater determ inants) involved in the fundam ental transition for N = 2 and N = 3 for (a) non-interacting and (b) interacting electrons in a magnetic eld. In the interacting case only the two most weighted con gurations are shown. (c) SE scattering rates between selected Fock-D arw in orbitals vsm agnetic eld. QD parameters are the same as in Fig. 3.



FIG.5: Charge relaxation rate vsm agnetic eld for N = 2 and N = 3 in a QD with  $L_z = 15$  nm and  $h!_0 = 5$  m eV. Insets: lowest-lying energy levels along with their quantum numbers (M;S); arrows indicate the transition under study.



FIG. 6: Charge relaxation rate vs interdot barrier thickness  $L_b$  in a CQD with  $L_z = 5 \text{ nm}$ ,  $h!_0 = 5 \text{ m}$  eV and N = 1;2;3 electrons. Solid lines: total scattering rate. D ashed line: DP contribution. D otted lines: PZ contribution. Note the di erent vertical scale in each panel. Next to the right axis, we indicate the quantum numbers (M;G;S) of the states involved in the transition. For N = 2, the PZ contribution cannot be distinguished on this scale. Insets: lowest-lying symmetric (solid line) and antisymmetric (dashed line) energy levels.



FIG.7: Energy of the em itted phonon vs interdot barrier thickness  $L_b$  for N = 2 interacting (solid line) and non-interacting (dashed line) electrons in the CQD structure of Fig. 6. The diagram s illustrate the dom inant SE con gurations with and without C oulom b interaction.